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# 2SJ76, 2SJ77, 2SJ78, 2SJ79

Silicon P-Channel MOS FET

# HITACHI

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## Application

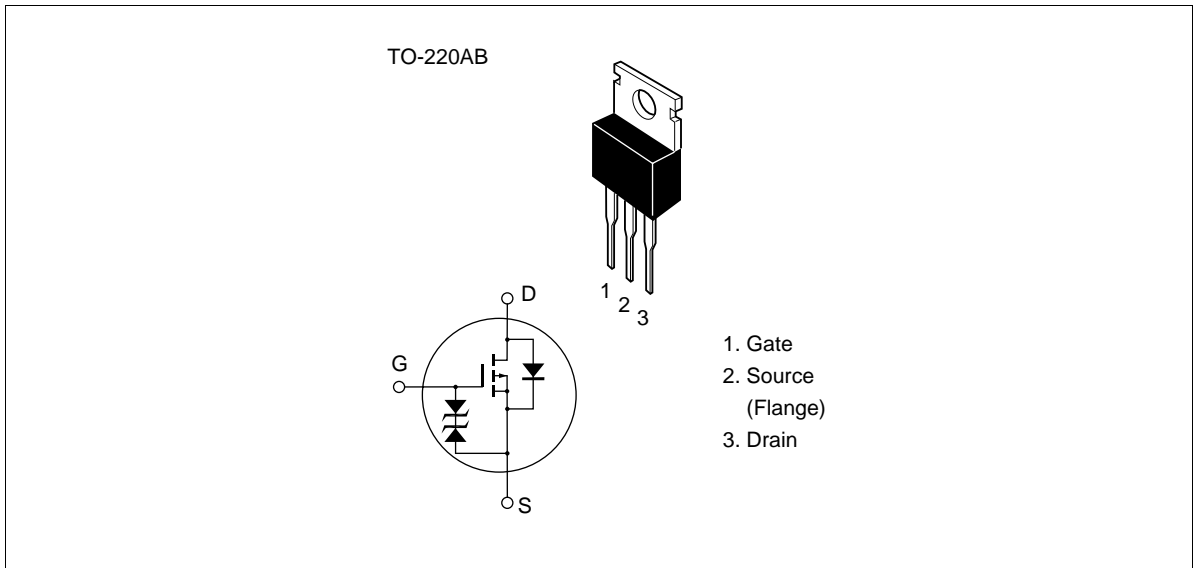
High frequency and low frequency power amplifier, high speed power switching

Complementary pair with 2SK213, 2SK214, 2SK215, 2SK216

## Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

## Outline



## 2SJ76, 2SJ77, 2SJ78, 2SJ79

### Absolute Maximum Ratings (Ta = 25°C)

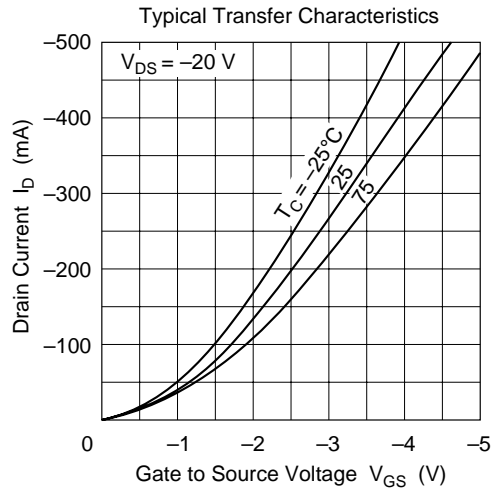
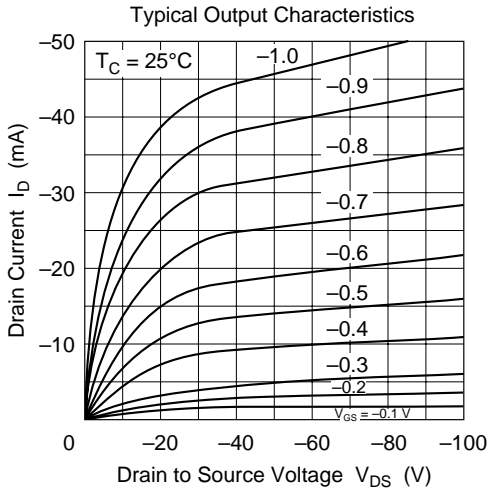
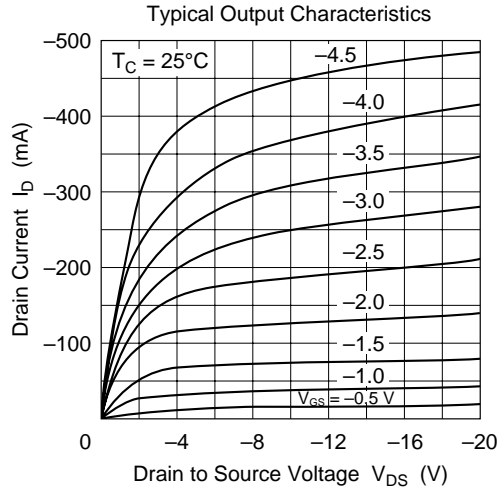
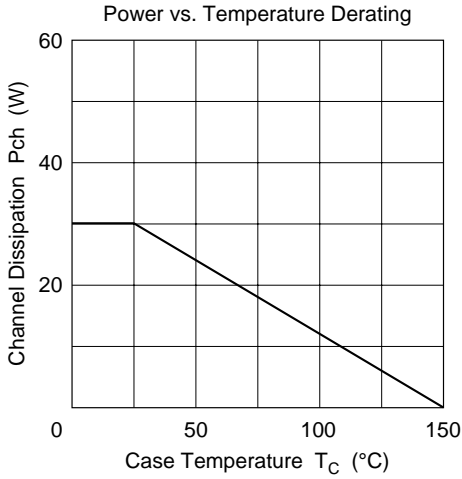
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ76	$V_{DSX}$	-140	V
	2SJ77		-160	
	2SJ78		-180	
	2SJ79		-200	
Gate to source voltage		$V_{GSS}$	±15	V
Drain current		$I_D$	-500	mA
Body to drain diode reverse drain current		$I_{DR}$	-500	mA
Channel dissipation		Pch	1.75	W
		$Pch^{*1}$	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-45 to +150	°C

Note: 1. Value at  $T_C = 25^\circ\text{C}$

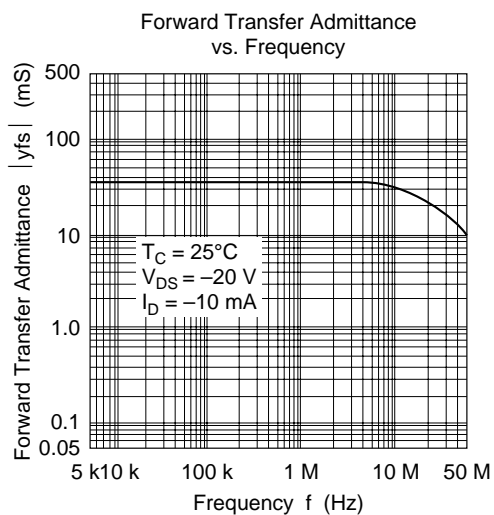
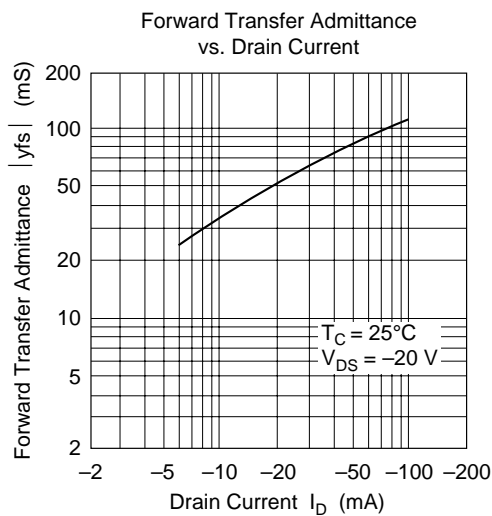
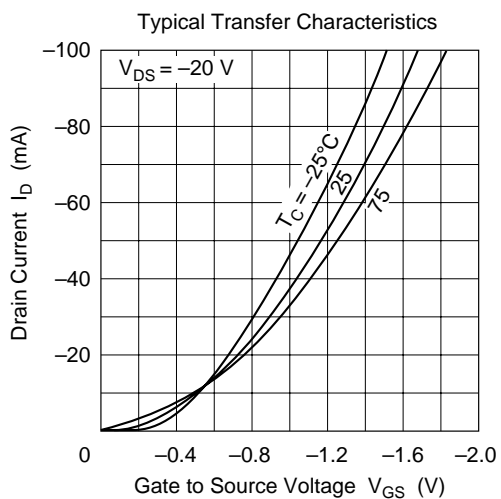
### Electrical Characteristics (Ta = 25°C)

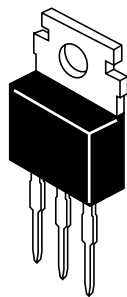
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ76	$V_{(BR)DSX}$	-140	—	—	V	$V_{GS} = 2\text{ V}, I_D = -1\text{ mA}$
	2SJ77		-160	—	—	V	
	2SJ78		-180	—	—	V	
	2SJ79		-200	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	±15	—	—	V	$I_G = \pm 10\ \mu\text{A}, V_{DS} = 0$
Gate to source voltage		$V_{GS(on)}$	-0.2	—	-1.5	V	$I_D = -10\text{ mA}, V_{DS} = -10\text{ V}^{*1}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-2.0	V	$I_D = -10\text{ mA}, V_{GD} = 0\text{ }^{*1}$
Forward transfer admittance		$ y_{fs} $	20	35	—	mS	$I_D = -10\text{ mA}, V_{DS} = -20\text{ V}^{*1}$
Input capacitance		Ciss	—	120	—	pF	$V_{DS} = -10\text{ V}, I_D = -10\text{ mA},$
Reverse transfer capacitance		Crss	—	4.8	—	pF	$f = 1\text{ MHz}$

Note: 1. Pulse test



# 2SJ76, 2SJ77, 2SJ78, 2SJ79





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      North America      : <http://semiconductor.hitachi.com/>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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